

IN THE SPECIFICATION

On page 1, after the title “Nitride Metal Oxide Semiconductor Integrated Transistor Devices” and prior to the header “Abstract”, please insert the following paragraph:

-- CROSS REFERENCE TO RELATED APPLICATIONS

This application is a U.S. national stage entry of international application PCT/US2004/38582 filed November 17, 2004, which claims priority to U.S. Provisional Application Number 60/520,322, attorney docket number OSEM–DB15P-US, filed November 17, 2003, now abandoned; international application PCT/US04/38582 filed November 17, 2004 also claims priority to U.S. Provisional Application Number 60/527,306, attorney docket number OSEM–DB16P-US, filed December 8, 2003, now abandoned. --